- ★ Super Low Gate Charge
- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

Green

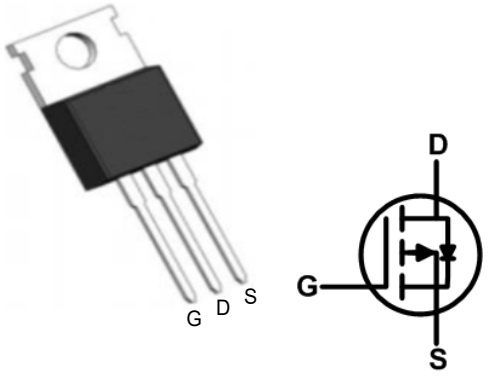
BVDSS	RDSON	ID
-100V	24.5mΩ	-80A

Description

The XR80P10T is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The XR80P10T meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

TO220AB Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1,6]	-80	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1,6]	-35	A
I_{DM}	Pulsed Drain Current[2]	-200	A
EAS	Single Pulse Avalanche Energy[3]	281	mJ
I_{AS}	Avalanche Current	-37	A
P_D@T_C=25℃	Total Power Dissipation[4]	147	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	---	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	---	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-100	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	---	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-10V , I_D=-1A	---	24.5	30	mΩ
		V_{GS}=-10V , I_D=-1A	---	27	35	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.2	-1.85	-2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	---	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-100V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=-100V, V_{GS}=0V , T_J=100℃	---	---	---	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-10V , I_D=-20A	---	60	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	5	---	Ω
Q_g	Total Gate Charge	V_{DS}=-50V , V_{GS}=-10V , I_D=-20A	---	196	---	nC
Q_{gs}	Gate-Source Charge		---	25.5	---	
Q_{gd}	Gate-Drain Charge		---	41.5	---	
$T_{d(on)}$	Turn-On Delay Time	V_{GS}=-10V, V_{DS}=-50V, I_D=-20A, R_G=3Ω	---	20	---	ns
T_r	Rise Time		---	50	---	
$T_{d(off)}$	Turn-Off Delay Time		---	120	---	
T_f	Fall Time		---	198	---	
C_{iss}	Input Capacitance	V_{DS}=-50V , V_{GS}=0V , f=1MHz	---	8650	---	pF
C_{oss}	Output Capacitance		---	250	---	
C_{rss}	Reverse Transfer Capacitance		---	215	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,4]	V_G=V_D=0V , Force Current	---	---	-30	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-20A , T_J=25C	---	---	-1.2	V

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C.
2. The EAS data shows Max. rating . The test condition is V_{DD}= -30V, V_{GS}= -10V, L= 0.4mH,
3. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
5. This value is guaranteed by design hence it is not included in the production test..

Typical Performance Characteristics

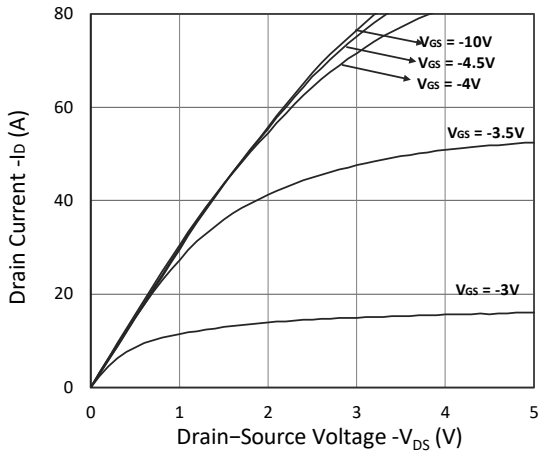


Figure 1. Output Characteristics

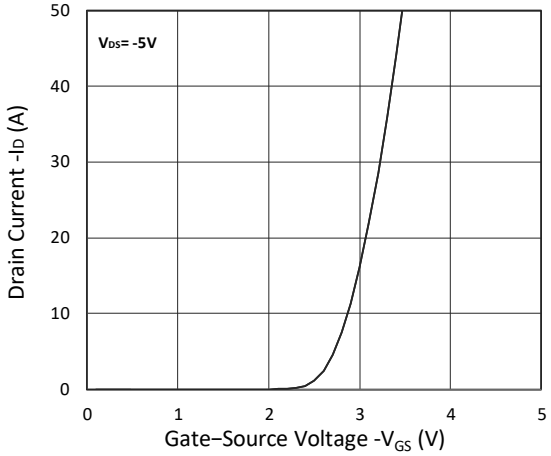


Figure 2. Transfer Characteristics

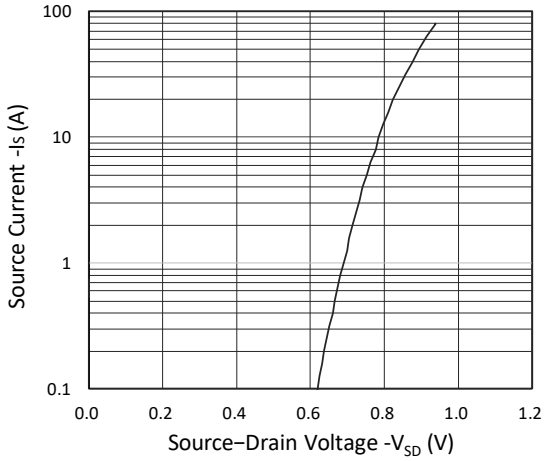


Figure 3. Forward Characteristics of Reverse

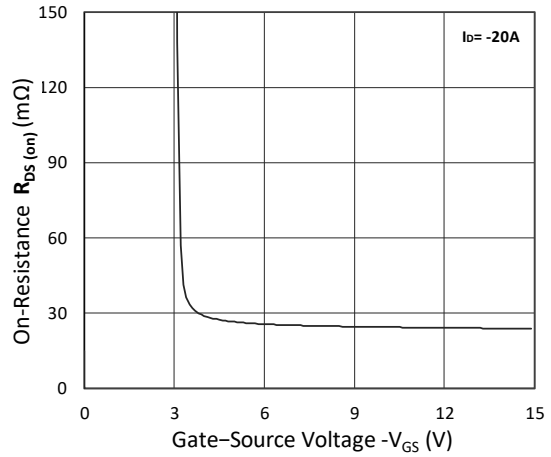


Figure 4. $R_{DS(on)}$ vs. V_{GS}

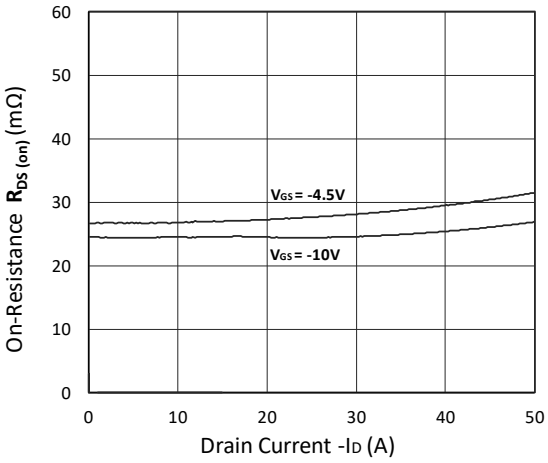


Figure 5. $R_{DS(on)}$ vs. I_D

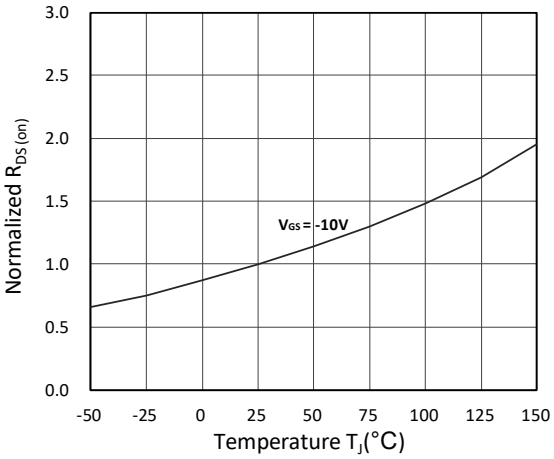


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

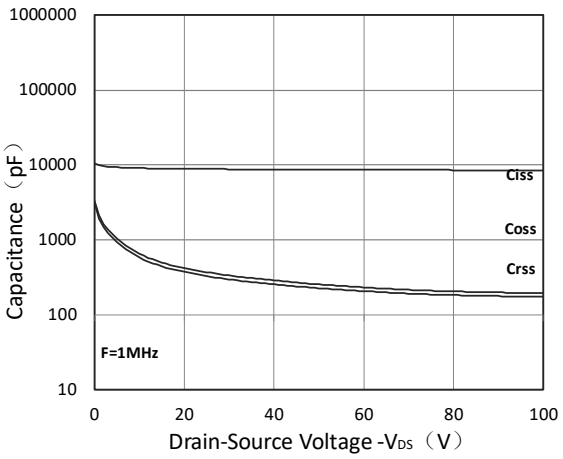


Figure 7. Capacitance Characteristics

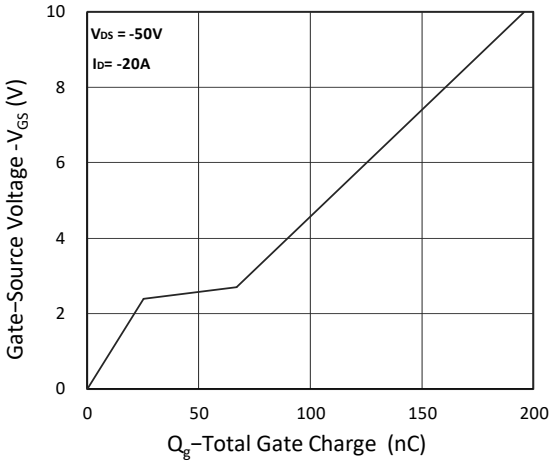


Figure 8. Gate Charge Characteristics

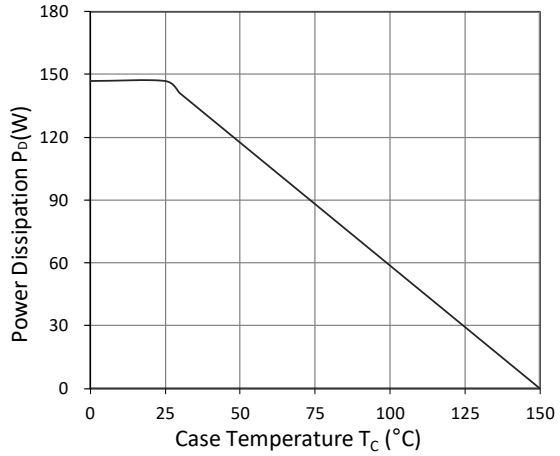


Figure 9. Power Dissipation

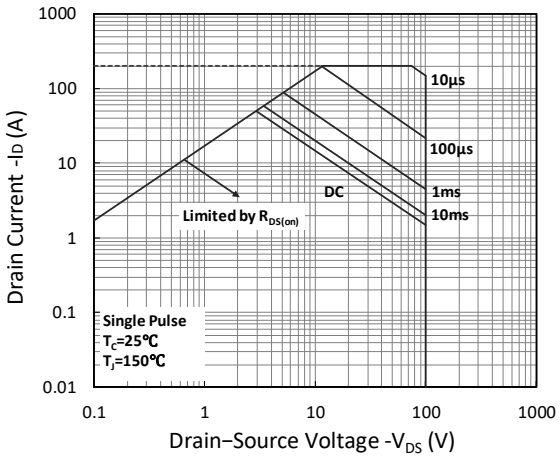


Figure10. Safe Operating Area

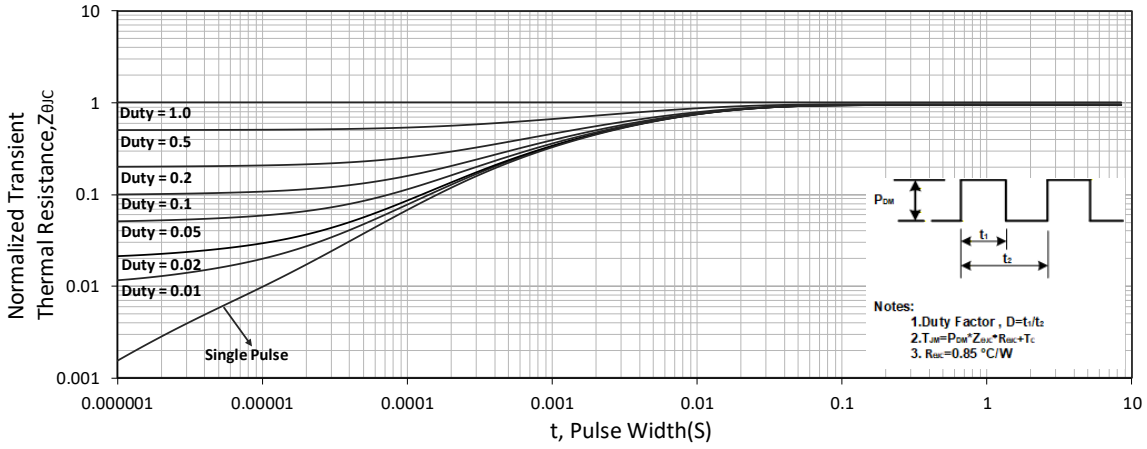
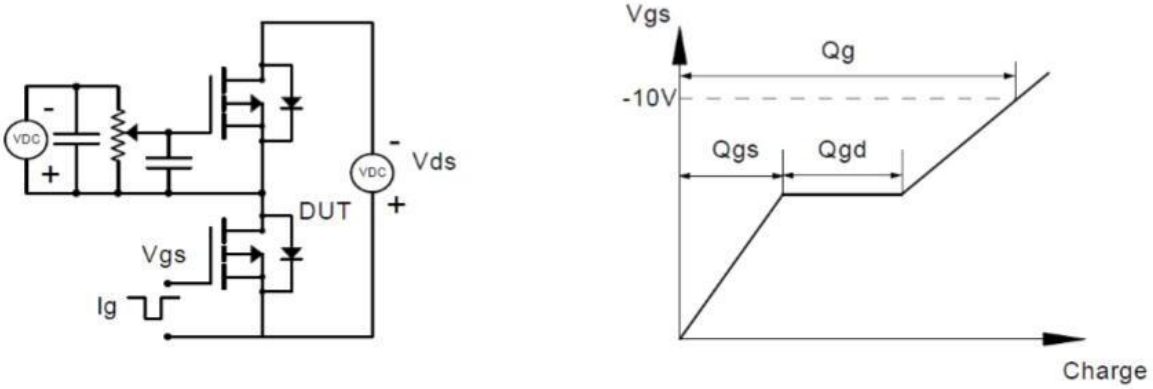


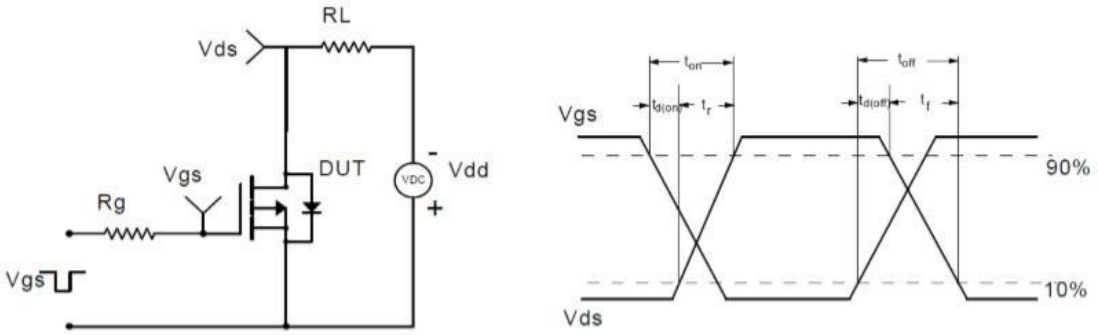
Figure 11. Normalized Maximum Transient Thermal Impedance

Test Circuit & Waveform

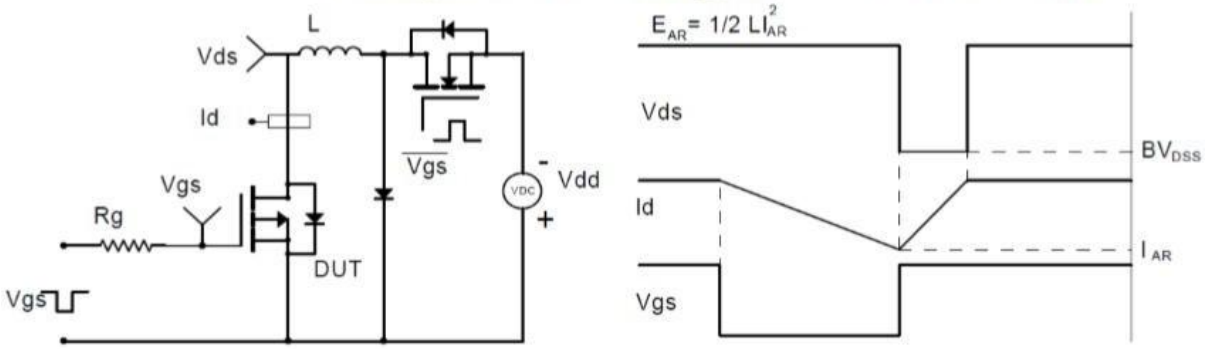
Gate Charge Test Circuit & Waveform



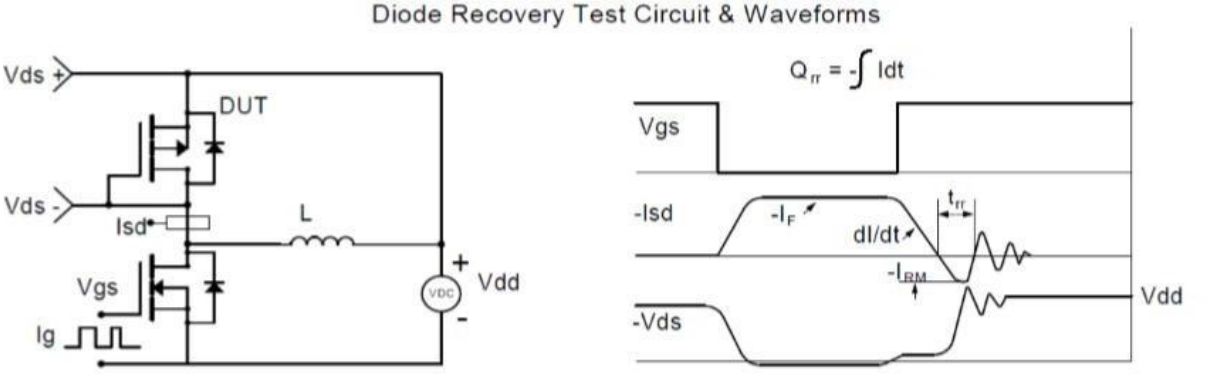
Resistive Switching Test Circuit & Waveforms



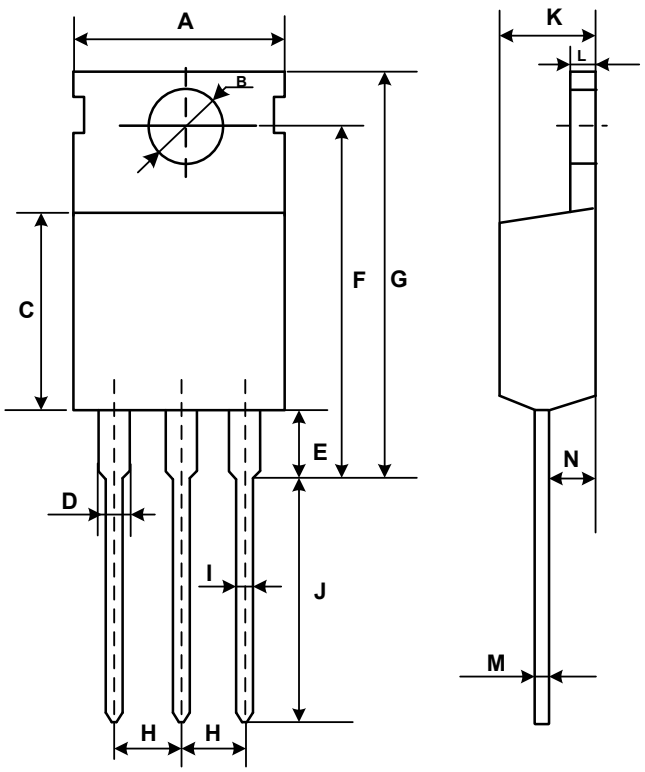
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Mechanical Dimensions for TO-220



OMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	9.70	10.30
B	3.40	3.80
C	8.80	9.40
D	1.17	1.47
E	2.60	3.50
F	15.10	16.70
G	19.55MAX	
H	2.54REF	
I	0.70	0.95
J	9.35	11.00
K	4.30	4.77
L	1.20	1.45
M	0.40	0.65
N	2.20	2.60